

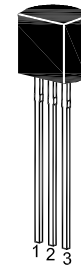
2SC3279

NPN Silicon Epitaxial Planar Transistor

for storobo flash and medium power amplifier applications.

The transistor is subdivided into four groups L, M, N and P, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CES}	30	V
Collector Emitter Voltage	V_{CEO}	10	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse Width = 10 ms)	I_{CP}	5	A
Base Current	I_B	0.2	A
Power Dissipation	P_{tot}	750	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V _{CE} = 1 V, I _C = 500 mA Current Gain Group at V _{CE} = 1 V, I _C = 2 A	L h _{FE}	140	-	240	-
	M h _{FE}	200	-	330	-
	N h _{FE}	300	-	450	-
	P h _{FE}	420	-	600	-
	h _{FE}	70	200	-	-
Collector Base Cutoff Current at V _{CB} = 30 V	I _{CBO}	-	-	0.1	μA
Emitter Base Cutoff Current at V _{EB} = 6 V	I _{EBO}	-	-	0.1	μA
Collector-Emitter Breakdown Voltage at I _C = 10 mA	V _{(BR)CEO}	10	-	-	V
Emitter Base Breakdown Voltage at I _E = 1 mA	V _{(BR)EBO}	6	-	-	V
Collector Emitter Saturation Voltage at I _C = 2 A, I _B = 50 mA	V _{CE(sat)}	-	0.2	0.5	V
Base Emitter Voltage at V _{CE} = 1 V, I _C = 2 A	V _{BE}	-	0.86	1.5	V
Collector Output Capacitance at V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	27	-	pF
Transition Frequency at V _{CE} = 1 V, I _C = 0.5 A	f _T	-	150	-	MHz

